

# Contents

<b>1. Introduction</b>	<b>1</b>
<b>2. Fundamentals of SRAM and Sensing</b>	<b>5</b>
2.1 Static Random Access Memory (SRAM)	5
2.2 Methods of Sensing: Voltage Sensing - Current Sensing	8
2.3 Sensing Delay	10
2.4 Summary	13
<b>3. Voltage Sense Amplifiers</b>	<b>15</b>
3.1 Principles and Typical Circuits	15
3.1.1 Static Voltage Sense Amplifiers (Static Comparators)	15
3.1.2 Dynamic Voltage Sense Amplifiers (Latch-Type Sense Amplifiers)	16
3.2 A Latch-Type Sense Amplifier for Current Sensed SRAM	20
3.2.1 Circuit Description	20
3.2.2 Delay	22
3.2.3 Yield	25
3.2.4 Yield Improvement	28
3.2.5 Optimum Input DC level $V_{INDC}$	31
3.2.6 Transistor Sizing, Temperature	34
3.2.7 Comparison to Conventional Latch	35
3.2.8 Design Guideline	36
3.3 Summary	36
<b>4. Circuit Principles for Current Sensing</b>	<b>39</b>
4.1 Introduction	39
4.2 Type A - Cascode and Diode Connection	41
4.3 Type B - Regulated Cascode	44
4.3.1 Single-Ended Current Sensing	44
4.3.2 Differential Current Sensing	48
4.3.3 Delay	49
4.4 Type C - Negative Impedance Converter	54
4.4.1 Single-Ended Current Sensing	54
4.4.2 Differential Current Sensing	58

4.4.3	Delay .....	60
4.4.4	Implementation Examples .....	62
4.5	Type D - Wilson Type .....	64
4.5.1	Single-Ended Current Sensing .....	64
4.5.2	Differential Current Sensing .....	67
4.5.3	Delay .....	69
4.6	Offset Comparison Between Type B and D .....	71
4.7	Conclusion .....	75
4.7.1	Delay Comparison .....	75
4.7.2	Future Technologies .....	76
4.7.3	Small-Signal Versus Large-Signal Analysis .....	76
4.7.4	Overall Comparison .....	77
4.8	Summary .....	78
<b>5.</b>	<b>Analysis and Compensation of the Bitline Multiplexer ....</b>	<b>81</b>
5.1	Introduction .....	81
5.2	Analysis of the Multiplexer .....	82
5.2.1	General Considerations .....	82
5.2.2	Analysis for $r_s = 0$ .....	83
5.2.3	Analysis for $r_s \neq 0$ .....	84
5.3	Principle of Multiplexer Compensation .....	88
5.4	Type D .....	88
5.4.1	Behavior with Multiplexer .....	88
5.4.2	Multiplexer Compensation .....	90
5.4.3	Step Response .....	93
5.5	Type B .....	94
5.6	Type A and C .....	95
5.7	Experimental Results .....	97
5.8	Summary .....	99
<b>6.</b>	<b>Interaction with the Memory Cell .....</b>	<b>101</b>
6.1	Stability .....	101
6.1.1	Mechanism of Cell Instability .....	101
6.1.2	Critical Bitline Voltage .....	104
6.1.3	Technology Trend .....	106
6.2	Cell Current .....	107
6.3	Summary .....	108
<b>7.</b>	<b>Implementation Aspects .....</b>	<b>109</b>
7.1	Design Procedure .....	110
7.2	Circuit Characterization .....	113
7.3	Power-Down and Precharge .....	116
7.4	System Performance .....	121
7.5	Summary .....	125

<b>8. Outlook</b> .....	127
<b>A. Two-Pole Transfer Function</b> .....	129
<b>B. Step Response</b> .....	131
<b>C. Common-Mode Stability</b> .....	135
<b>D. Delay Versus Supply Voltage</b> .....	141
<b>E. Experimental Results: Current Sensing</b> .....	145
<b>F. Experimental Results: Voltage Sensing</b> .....	149
<b>Bibliography</b> .....	150
<b>Index</b> .....	159

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